

International

IOR Rectifier

HEXFET® POWER MOSFET

Provisional Data Sheet No. PD-9.548B

JANTX2N6806

JANTXV2N6806

[REF:MIL-PRF-19500/562]

[GENERIC:IRF9230]

P-CHANNEL

-200 Volt, 0.80Ω HEXFET

HEXFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry achieves very low on-state resistance combined with high transconductance. HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits, and virtually any application where high reliability is required.

Product Summary

Part Number	BV _{DS}	R _{DS(on)}	I _D
JANTX2N6806	-200V	0.80Ω	-6.5A
JANTXV2N6806			

Features:

- Avalanche Energy Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

	Parameter	JANTX2N6806, JANTXV2N6806	Units
I _D @ V _{GS} = -10V, T _C = 25°C	Continuous Drain Current	-6.5	A
I _D @ V _{GS} = -10V, T _C = 100°C	Continuous Drain Current	-4.0	
I _{DM}	Pulsed Drain Current ①	-28	
P _D @ T _C = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.60	W/K ②
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy ②	66	mJ
I _{AR}	Avalanche Current ①	-6.5	A
E _{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10.5 seconds)	
	Weight	11.5 (typical)	g

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Electrical Characteristics @ T_J = 25°C (Unless Otherwise Specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BVDSS	Drain-to-Source Breakdown Voltage	-200	—	—	V	V _{GS} = 0V, I _D = -1.0 mA
ΔBVDSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	-0.20	—	V/°C	Reference to 25°C, I _D = -1.0 mA
RDS(on)	Static Drain-to-Source On-State Resistance	—	—	0.80	Ω	V _{GS} = -10V, I _D = -4.0A④
VGS(th)	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
gfs	Forward Transconductance	2.0	—	—	S (Ω)	V _{DS} > -15V, I _{DS} = -4.0A ④
IDSS	Zero Gate Voltage Drain Current	—	—	-25	μA	V _{DS} = 0.8 x Max Rating, V _{GS} = 0V
		—	—	-250	μA	V _{DS} = 0.8 x Max Rating V _{GS} = 0V, T _J = 125°C
IGSS	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
IGSS	Gate-to-Source Leakage Reverse	—	—	100	nA	V _{GS} = 20V
Qg	Total Gate Charge	8	—	31	nC	V _{GS} = -10V, I _D = -6.5A
Qgs	Gate-to-Source Charge	0.8	—	7.0	nC	V _{DS} = Max. Rating x 0.5 see figures 6 and 13
Qgd	Gate-to-Drain ("Miller") Charge	5.0	—	17	nC	
td(on)	Turn-On Delay Time	—	—	50	ns	V _{DD} = -100V, I _D = -6.5A, R _G = 7.5Ω, V _{GS} = -10V
tr	Rise Time	—	—	100	ns	
td(off)	Turn-Off Delay Time	—	—	100	ns	
tf	Fall Time	—	—	80	ns	see figure 10
LD	Internal Drain Inductance	—	5.0	—	nH	Measured from the drain lead, 6mm (0.25 in.) from package to center of die.
LS	Internal Source Inductance	—	13.0	—	nH	Measured from the source lead, 6mm (0.25 in.) from package to source bonding pad.
Ciss	Input Capacitance	—	700	—	pF	V _{GS} = 0V, V _{DS} = -25V
Coss	Output Capacitance	—	200	—	pF	f = 1.0 MHz
Crss	Reverse Transfer Capacitance	—	40	—	pF	see figure 5

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-6.5	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier.
ISM	Pulse Source Current (Body Diode) ①	—	—	-28	A	
VSD	Diode Forward Voltage	—	—	-6.0	V	T _J = 25°C, I _S = -6.5A, V _{GS} = 0V ④
trr	Reverse Recovery Time	—	—	400	ns	T _J = 25°C, I _F = -6.5A, di/dt ≤ -100A/μs
QRR	Reverse Recovery Charge	—	—	4.0	μC	V _{DD} ≤ -50V ④
ton	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	1.67	°C/W	
R _{thJA}	Junction-to-Ambient	—	—	30	°C/W	Typical socket mount

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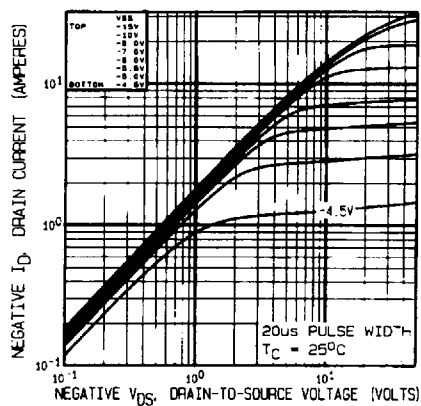


Fig. 1 — Typical Output Characteristics
 $T_C = 25^\circ\text{C}$

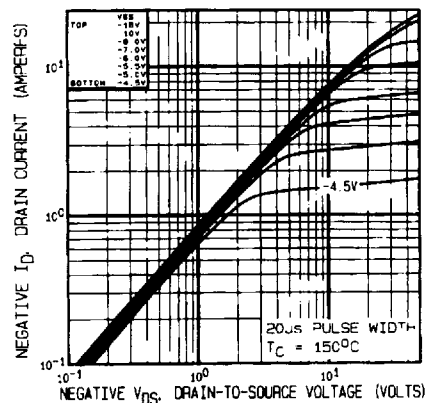


Fig. 2 — Typical Output Characteristics
 $T_C = 150^\circ\text{C}$

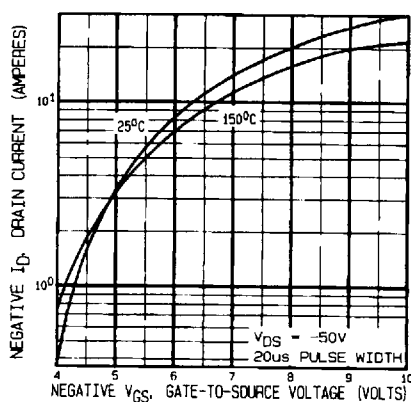


Fig. 3 — Typical Transfer Characteristics

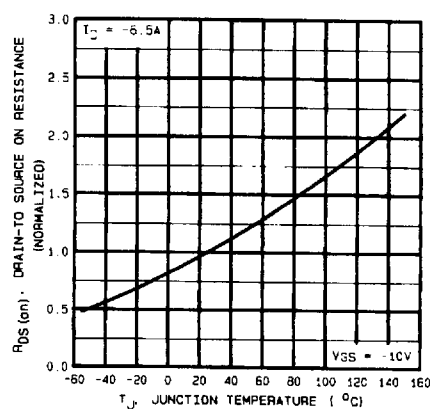


Fig. 4 — Normalized On-Resistance Vs. Temperature

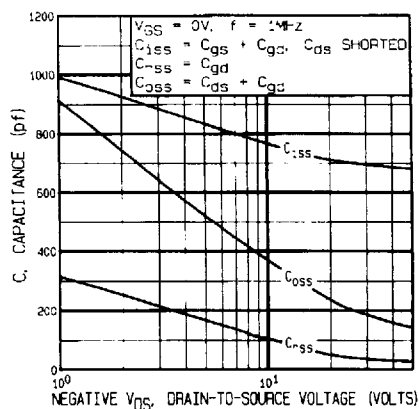


Fig. 5 — Typical Capacitance Vs. Drain-to-Source Voltage

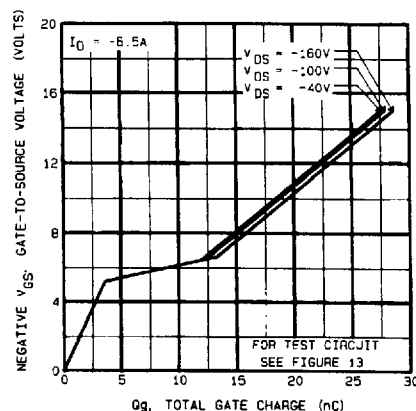


Fig. 6 — Typical Gate Charge Vs. Gate-to-Source Voltage

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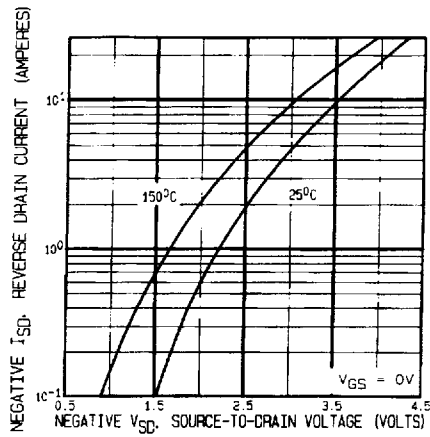


Fig. 7 — Typical Source-to-Drain Diode Forward Voltage

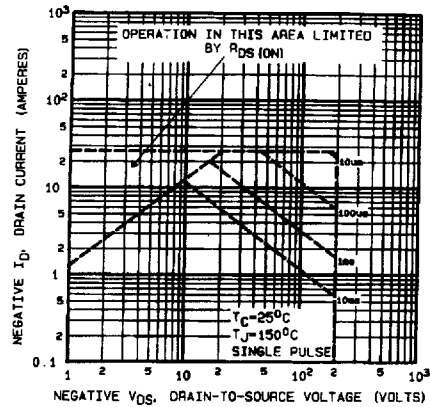


Fig. 8 — Maximum Safe Operating Area

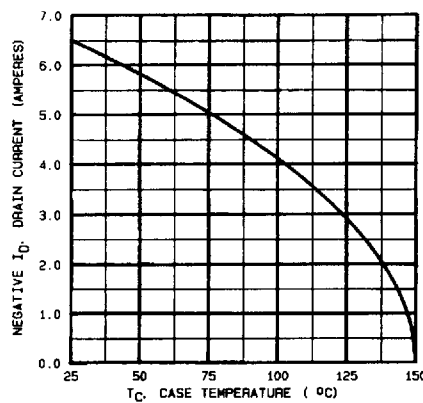


Fig. 9 — Maximum Drain Current Vs. Case Temperature

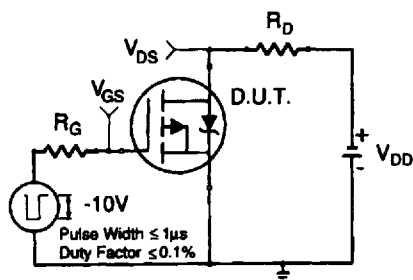


Fig. 10a — Switching Time Test Circuit

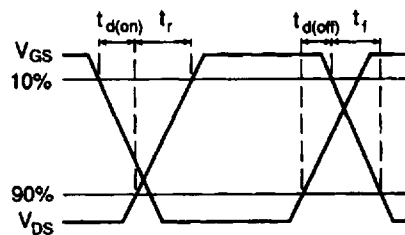


Fig. 10b — Switching Time Waveforms

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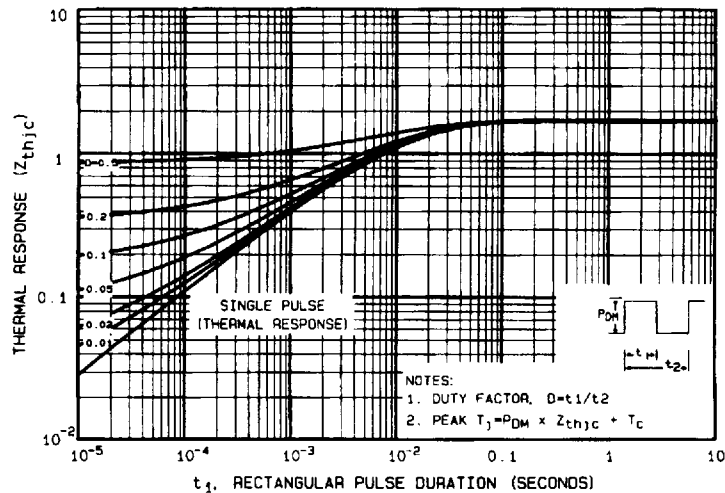


Fig. 11 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

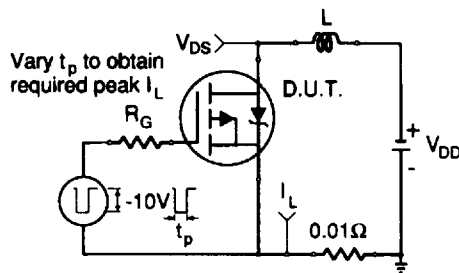


Fig. 12a — Unclamped Inductive Test Circuit

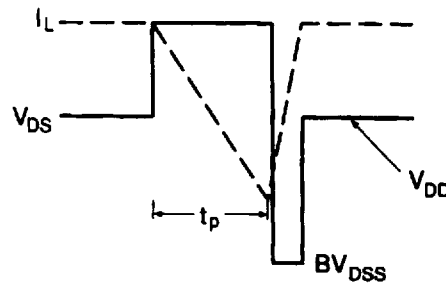


Fig. 12b — Unclamped Inductive Waveforms

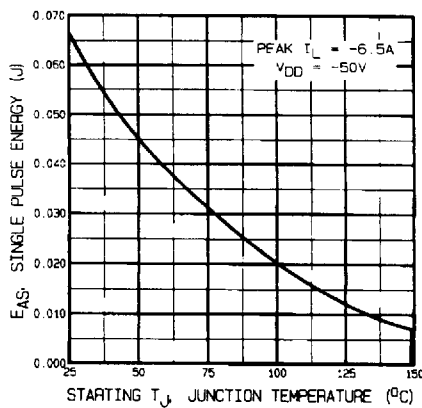


Fig. 12c — Max. Avalanche Energy vs. Current

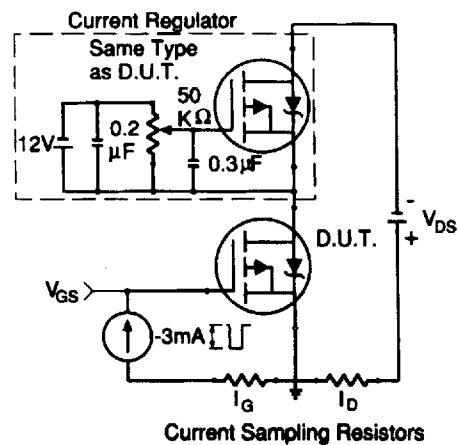


Fig. 13a — Gate Charge Test Circuit

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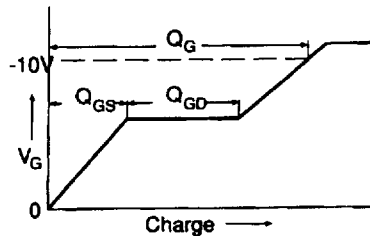
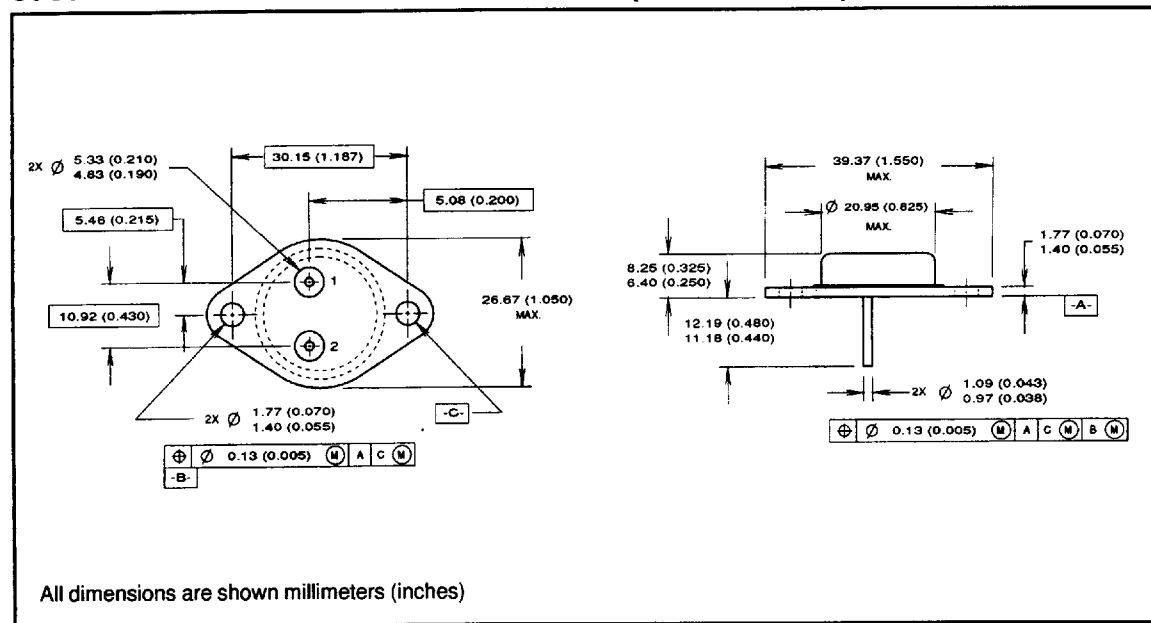


Fig. 13b — Basic Gate Charge Waveform

- ① Repetitive Rating; Pulse width limited by maximum junction temperature. (see figure 11)
- ② @ $V_{DD} = -50V$, Starting $T_J = 25^\circ C$,
 $EAS = [0.5 \cdot L \cdot (I_L^2) \cdot [BV_{DSS}/(BV_{DSS} - V_{DD})]]$
 Peak $I_L = -6.5A$, $V_{GS} = -10V$, $25 \leq R_G \leq 200\Omega$
- ③ $I_{SD} \leq -6.5A$, $di/dt \leq -120A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$

Case Outline and Dimensions — TO-204AA (Modified TO-3)



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WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331
EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

<http://www.irf.com/>

Data and specifications subject to change without notice.

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